

## isc N-Channel MOSFET Transistor

## AOK22N50

### • FEATURES

- With TO-247 packaging
- High speed switching
- Very high commutation ruggedness
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • APPLICATIONS

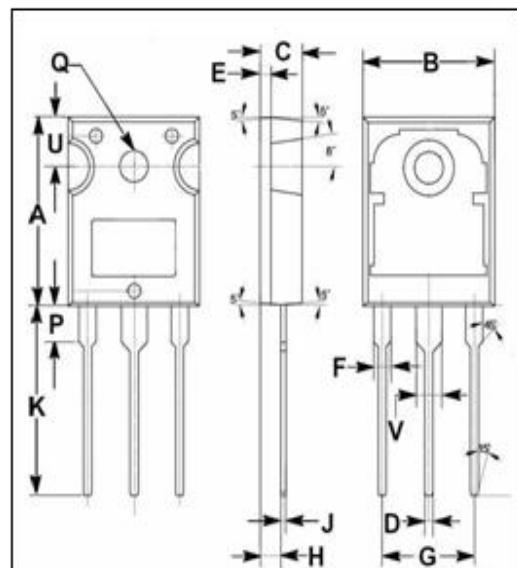
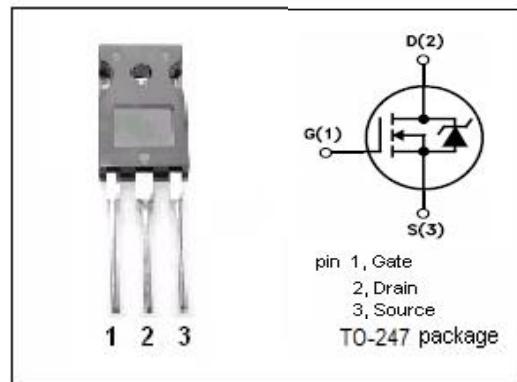
- PFC stages
- LCD & PDP TV
- Power supply
- Switching applications

### • ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage	500	V
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-Continuous@ $T_c=25^\circ\text{C}$ $T_c=100^\circ\text{C}$	22 15	A
$I_{DM}$	Drain Current-Single Pulsed	28	A
$P_D$	Total Dissipation	417	W
$T_j$	Operating Junction Temperature	-55~150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.3	$^\circ\text{C}/\text{W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	40	$^\circ\text{C}/\text{W}$



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

**isc N-Channel MOSFET Transistor****AOK22N50****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

<b>SYMBOL</b>	<b>PARAMETER</b>	<b>CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNIT</b>
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	500			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =5V; I <sub>D</sub> =0.25mA	3.4		4.5	V
R <sub>Ds(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =11A		0.21	0.26	Ω
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0V			±0.1	µ A
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 500V; V <sub>GS</sub> = 0V; T <sub>c</sub> =25°C V <sub>DS</sub> = 400V; V <sub>GS</sub> = 0V; T <sub>c</sub> =150°C			1 10	µ A
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =1A, V <sub>GS</sub> = 0 V			1.0	V

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